



# STW12NK90Z

## N-CHANNEL 900V - 0.72Ω - 11A TO-247 Zener-Protected SuperMESH™ Power MOSFET

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>	P <sub>w</sub>
STW12NK90Z	900 V	< 0.88 Ω	11 A	230 W

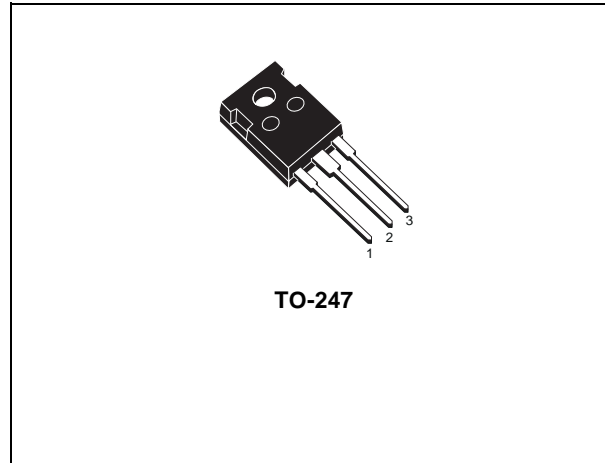
- TYPICAL R<sub>DS(on)</sub> = 0.72 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- GATE CHARGE MINIMIZED
- VERY LOW INTRINSIC CAPACITANCES
- VERY GOOD MANUFACTURING REPEATIBILITY

### DESCRIPTION

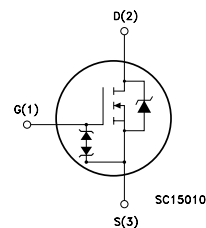
The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs including revolutionary MDmesh™ products.

### APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- IDEAL FOR OFF-LINE POWER SUPPLIES



### INTERNAL SCHEMATIC DIAGRAM



### ORDERING INFORMATION

SALES TYPE	MARKING	PACKAGE	PACKAGING
STW12NK90Z	W12NK90Z	TO-247	TUBE

**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	900	V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)	900	V
V <sub>GS</sub>	Gate- source Voltage	± 30	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 25°C	11	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 100°C	7	A
I <sub>DM</sub> (•)	Drain Current (pulsed)	44	A
P <sub>TOT</sub>	Total Dissipation at T <sub>C</sub> = 25°C	230	W
	Derating Factor	1.85	W/°C
V <sub>ESD(G-S)</sub>	Gate source ESD(HBM-C=100pF, R=1.5KΩ)	6000	V
dv/dt (1)	Peak Diode Recovery voltage slope	4.5	V/ns
T <sub>j</sub> T <sub>stg</sub>	Operating Junction Temperature Storage Temperature	-55 to 150	°C

(•) Pulse width limited by safe operating area

(1) I<sub>SD</sub> ≤ 11A, di/dt ≤ 200 A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>.

(\*) Limited only by maximum temperature allowed

**THERMAL DATA**

R <sub>thj-case</sub>	Thermal Resistance Junction-case Max	0.54	°C/W
R <sub>thj-amb</sub> T <sub>I</sub>	Thermal Resistance Junction-ambient Max Maximum Lead Temperature For Soldering Purpose	50 300	°C/W °C

**AVALANCHE CHARACTERISTICS**

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max)	11	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 50 V)	500	mJ

**GATE-SOURCE ZENER DIODE**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV <sub>GSO</sub>	Gate-Source Breakdown Voltage	I <sub>gs</sub> = ± 1mA (Open Drain)	30			V

**PROTECTION FEATURES OF GATE-TO-SOURCE ZENER DIODES**

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

**ELECTRICAL CHARACTERISTICS** (T<sub>CASE</sub> =25°C UNLESS OTHERWISE SPECIFIED)  
ON/OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 1 mA, V <sub>GS</sub> = 0	900			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating, T <sub>C</sub> = 125 °C			1 50	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 20V			±10	μA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 100 μA	3	3.75	4.5	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 5.5 A		0.72	0.88	Ω

**DYNAMIC**

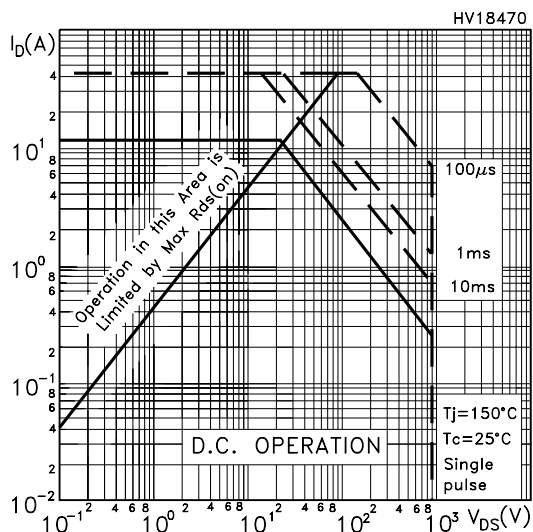
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (1)	Forward Transconductance	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 5.5 A		11		S
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V <sub>DS</sub> = 25V, f = 1 MHz, V <sub>GS</sub> = 0		3500 280 58		pF pF pF
C <sub>oss eq.</sub> (3)	Equivalent Output Capacitance	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V to 800V		117		pF
t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub>	Turn-on Delay Time Rise Time Turn-off Delay Time Fall Time	V <sub>DD</sub> = 450 V, I <sub>D</sub> = 5 A R <sub>G</sub> = 4.7Ω V <sub>GS</sub> = 10 V (Resistive Load see, Figure 3)		31 20 88 55		ns ns ns ns
Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub>	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V <sub>DD</sub> = 720V, I <sub>D</sub> = 10 A, V <sub>GS</sub> = 10V		113 19 60	152	nC nC nC

**SOURCE DRAIN DIODE**

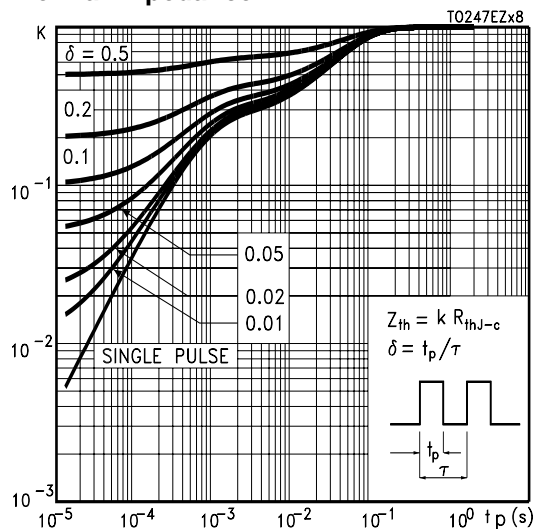
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I <sub>SD</sub> I <sub>SDM</sub> (2)	Source-drain Current Source-drain Current (pulsed)				11 44	A A
V <sub>SD</sub> (1)	Forward On Voltage	I <sub>SD</sub> = 11 A, V <sub>GS</sub> = 0			1.6	V
t <sub>rr</sub> Q <sub>rr</sub> I <sub>RRM</sub>	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I <sub>SD</sub> = 10 A, di/dt = 100A/μs V <sub>DD</sub> = 50 V (see test circuit, Figure 5)		728 7.8 21.6		ns μC A
t <sub>rr</sub> Q <sub>rr</sub> I <sub>RRM</sub>	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I <sub>SD</sub> = 10 A, di/dt = 100A/μs V <sub>DD</sub> = 50 V, T <sub>j</sub> = 150°C (see test circuit, Figure 5)		964 11 23		ns μC A

Note: 1. Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %.  
2. Pulse width limited by safe operating area.  
3. C<sub>oss eq.</sub> is defined as a constant equivalent capacitance giving the same charging time as C<sub>oss</sub> when V<sub>DS</sub> increases from 0 to 80% V<sub>DSS</sub>.

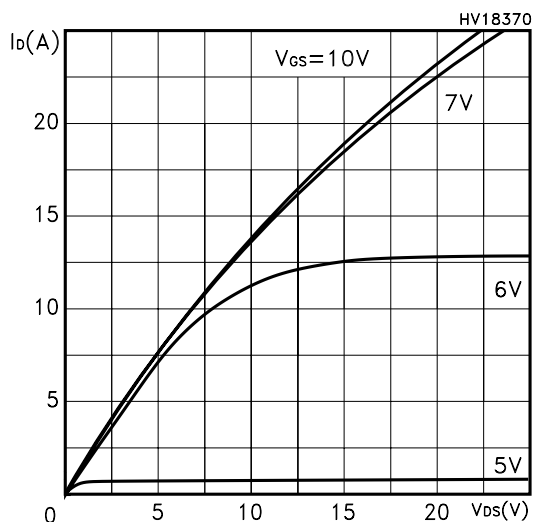
Safe Operating Area



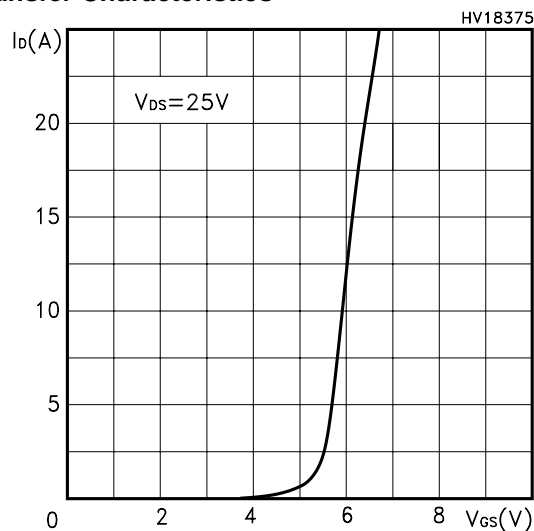
Thermal Impedance



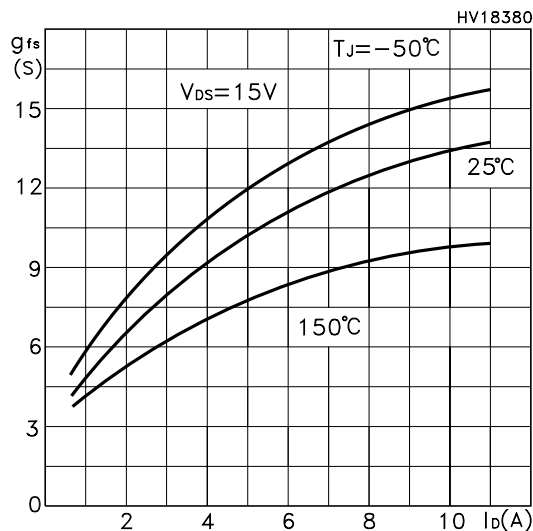
Output Characteristics



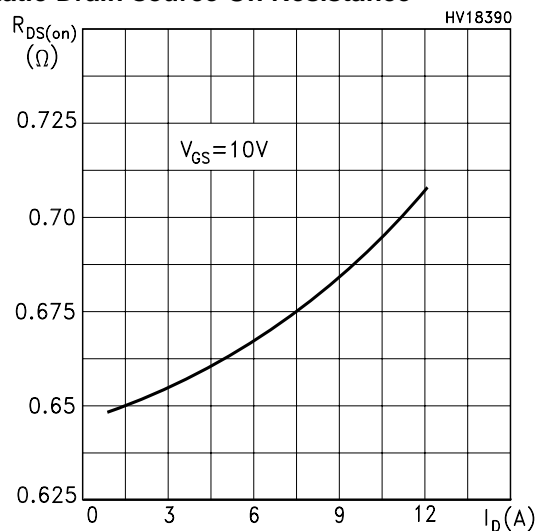
Transfer Characteristics



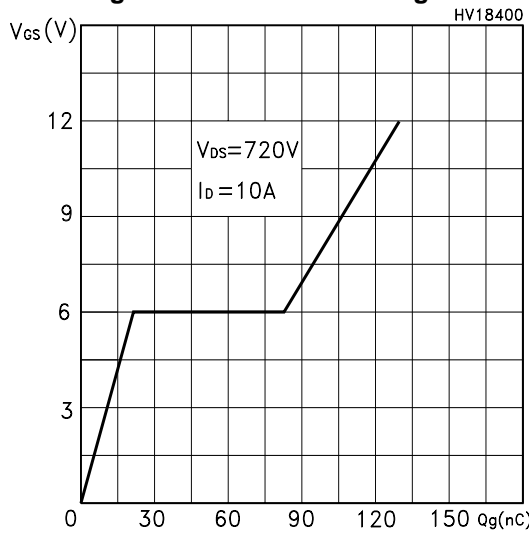
Transconductance



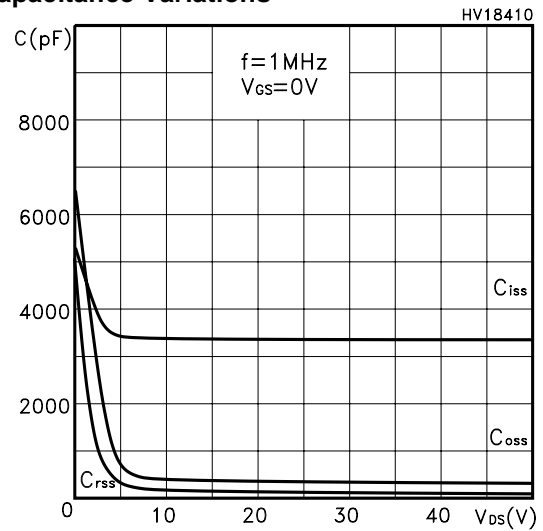
Static Drain-source On Resistance



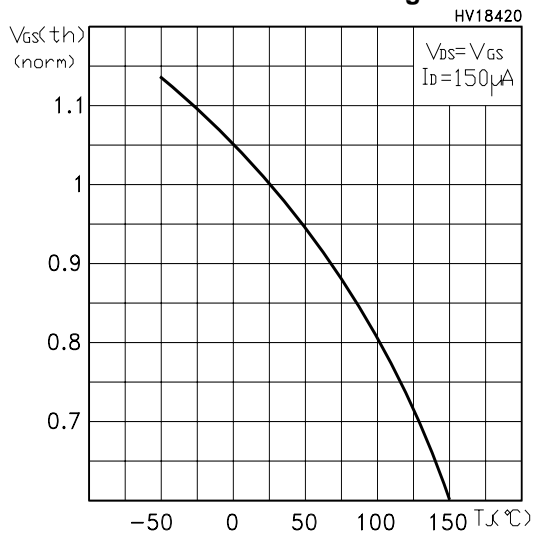
Gate Charge vs Gate-source Voltage



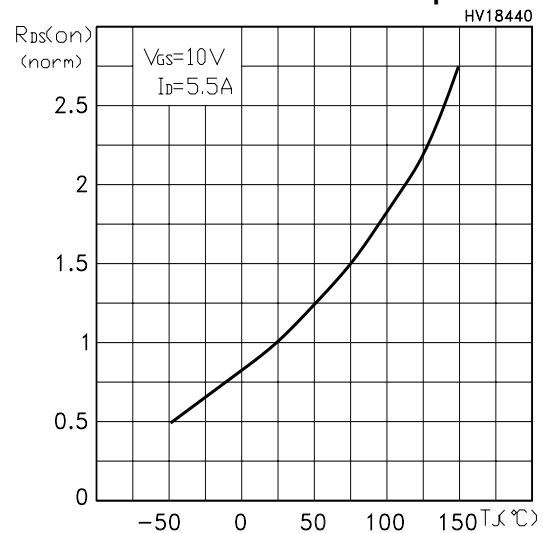
Capacitance Variations



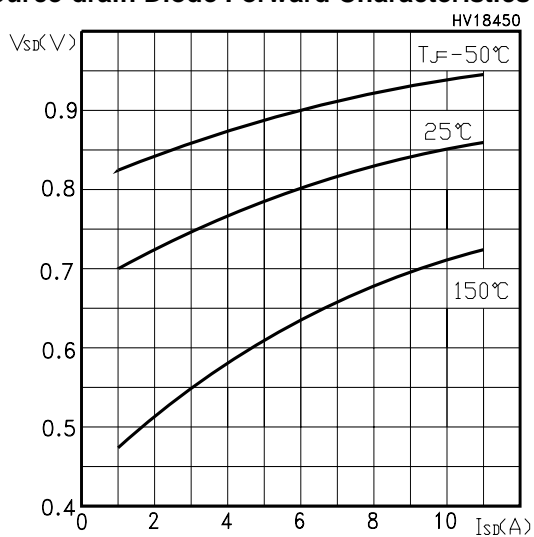
Normalized Gate Threshold Voltage vs Temp.



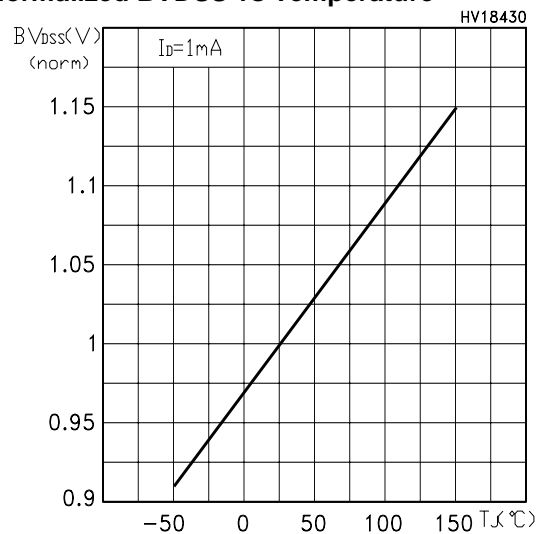
Normalized On Resistance vs Temperature



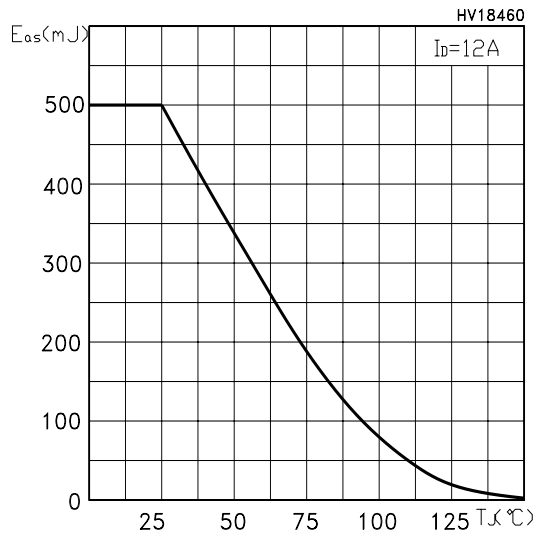
Source-drain Diode Forward Characteristics



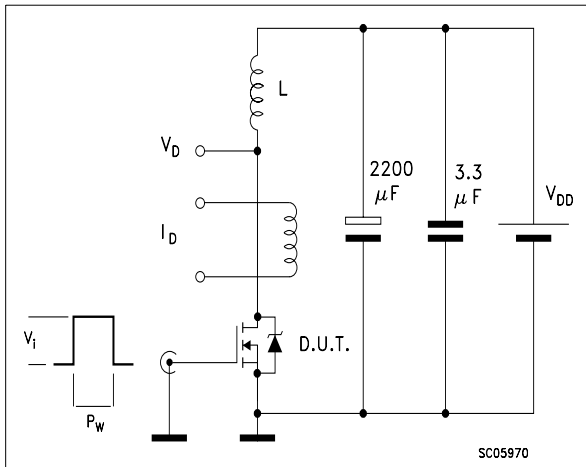
Normalized BVDSS vs Temperature



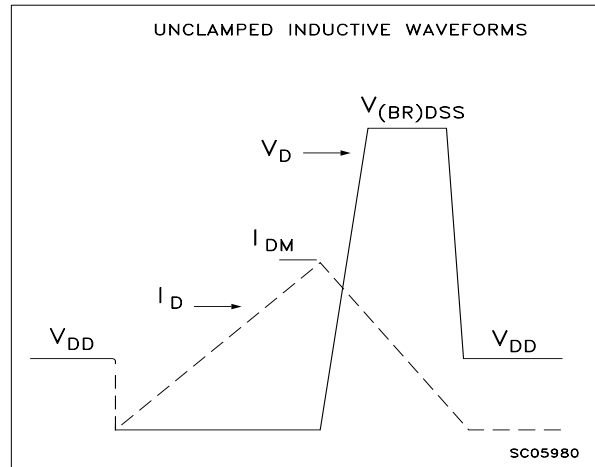
Maximum Avalanche Energy vs Temperature



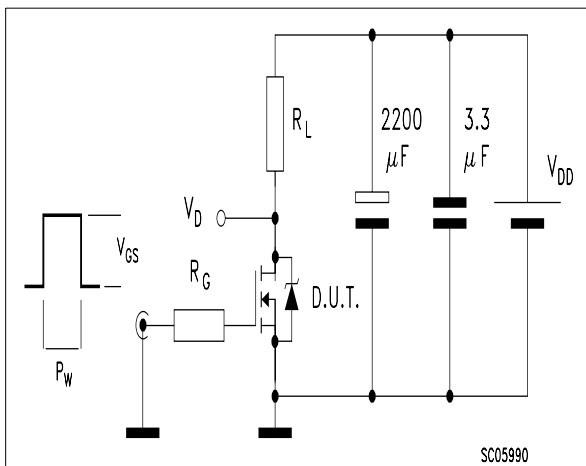
**Fig. 1: Unclamped Inductive Load Test Circuit**



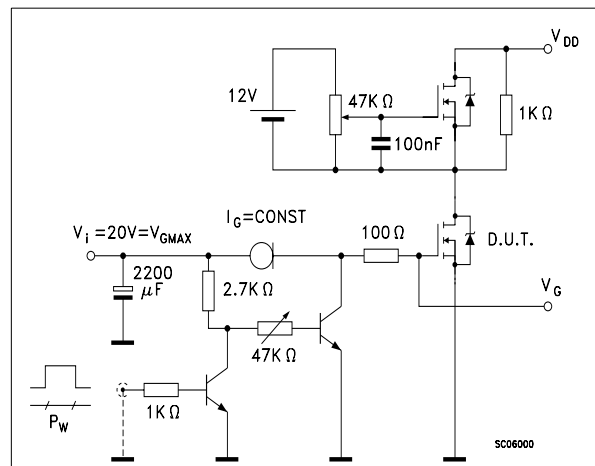
**Fig. 2: Unclamped Inductive Waveform**



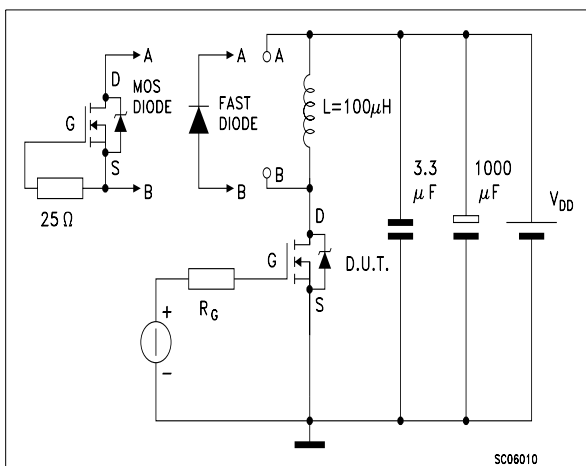
**Fig. 3: Switching Times Test Circuit For Resistive Load**



**Fig. 4: Gate Charge test Circuit**

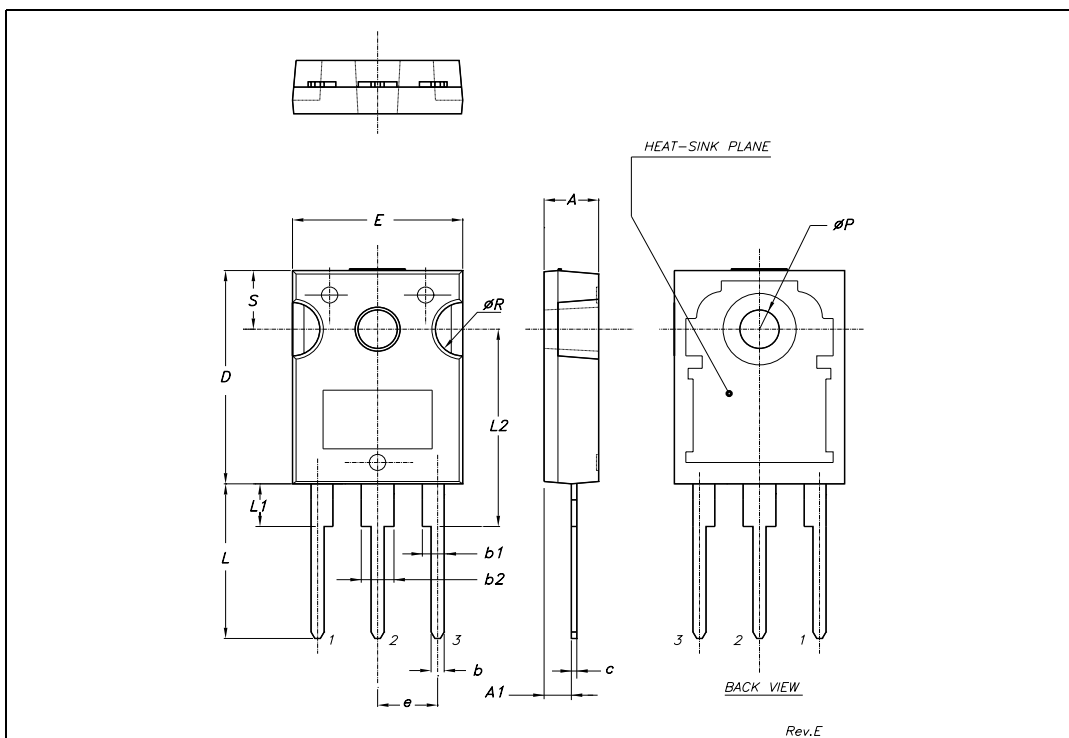


**Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times**



**TO-247 MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
c	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øP	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	





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